PNP Epitaxial Silicon Transistor

KSA928A

Features

- Audio Power Amplifier
- Complement to KSC2328A
- 3 W Output Application

ABSOLUTE MAXIMUM RATINGS

(Values are at $T_A = 25^{\circ}$ C unless otherwise noted.) (Notes 1, 2)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-2	Α
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

THERMAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.) (Note 3)

Symbol	Parameter	Value	Unit
P_{D}	Power Dissipation	1000	mW
	Derate Above 25°C	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	°C/W

3. PCB size: FR-4, 76 mm \times 114 mm \times 1.57 mm (3.0 inch \times 4.5 inch \times 0.062 inch) with minimum land pattern size.



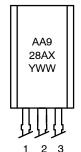
ON Semiconductor®

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TO-92 3 LF CASE 135AM

MARKING DIAGRAM



- 1: Emitter
- 2: Collector
- 3: Base

= Assembly Code A928A = Device Code = O/Y= Date Code

ORDERING INFORMATION

Device	Package	Shipping
KSA928AOTA	TO-92 3 LF (Pb-Free)	2000 / Fan–Fold
KSA928AYTA	TO-92 3 LF (Pb-Free)	2000 / Fan-Fold

KSA928A

ELECTRICAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-30	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -10 \text{ mA}, I_B = 0$	-30	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -1 \text{ mA}, I_C = 0$	-5	-	-	V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = -30 \text{ V}, I_{E} = 0$	-	-	-100	nA
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = -5 \text{ V}, I_C = 0$	-	-	-100	nA
h _{FE}	DC Current Gain	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	100	-	320	
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	-	-	-1.0	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -1.5 \text{ A}, I_B = -30 \text{ mA}$	-	-	-2.0	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -2 \text{ V}, I_{C} = -500 \text{ mA}$	-	120	-	MHz
C _{ob}	Collector Output Capacitance	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	-	48	_	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

hFE CLASSIFICATION

Classification	0	Y
h _{FE}	100 ~ 200	160 ~ 320

KSA928A

TYPICAL PERFORMANCE CHARACTERISTICS

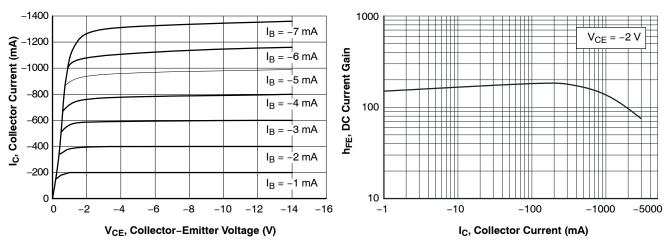


Figure 1. Static Characteristic

Figure 2. DC Current Gain

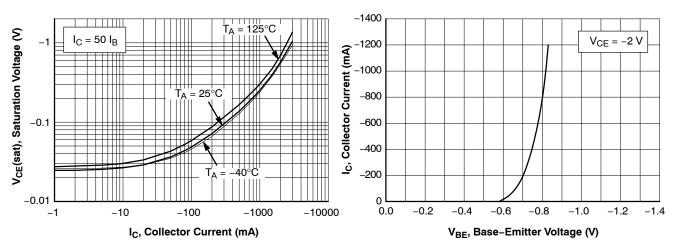
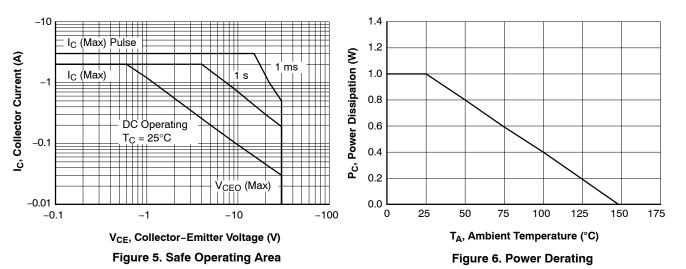
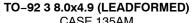


Figure 3. Collector-Emitter Saturation Voltage

Figure 4. Base-Emitter On Voltage





CASE 135AM ISSUE B

DATE 14 JAN 2021



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, GATE REMAINS AND TIE BAR PROTRUSIONS.
- 4. DIMENSION & AND &2 DOES NOT INCLUDE DAMBAR PROTRUSION.
 DIMENSION &2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	3.70	3.90	4.10	
A1	1.25	1.45	1.65	
b	0.35	0.50	0.60	
b2	0.62		0.78	
С	0.35	0.45	0.55	
D	7.80	8.00	8.20	
Ε	4.70	4.90	5.10	
E2	3.70	3.90	4.10	
е	1.27 BSC			
e2		2.50 BSC		
F		2.45 REF		
L		13.00 REF		
L2	1.50		1.90	
L3	2.60		3,40	
L4	10.40 REF			

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